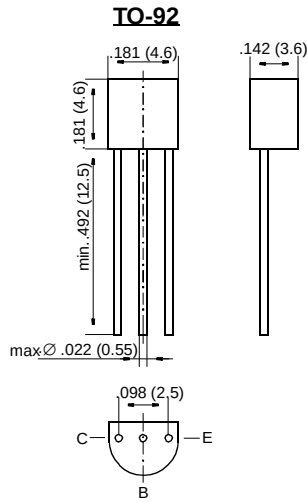


BC327, BC328

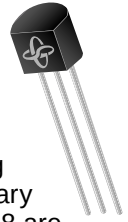
Small Signal Transistors (PNP)



Dimensions in inches and (millimeters)

FEATURES

- ◆ PNP Silicon Epitaxial Planar Transistors for switching and amplifier applications. Especially suitable for AF-driver stages and low-power output stages.
- ◆ These types are also available subdivided into three groups -16, -25, and -40, according to their DC current gain. As complementary types, the NPN transistors BC337 and BC338 are recommended.
- ◆ On special request, these transistors are also manufactured in the pin configuration TO-18.



MECHANICAL DATA

Case: TO-92 Plastic Package

Weight: approx. 0.18 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

		Symbol	Value	Unit
Collector-Emitter Voltage	BC327	$-V_{CES}$	50	V
	BC328	$-V_{CES}$	30	V
Collector-Emitter Voltage	BC327	$-V_{CEO}$	45	V
	BC328	$-V_{CEO}$	25	V
Emitter-Base Voltage		$-V_{EBO}$	5	V
Collector Current		$-I_C$	800	mA
Peak Collector Current		$-I_{CM}$	1	A
Base Current		$-I_B$	100	mA
Power Dissipation at $T_{amb} = 25\text{ °C}$		P_{tot}	625 ¹⁾	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_S	-65 to +150	°C

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

BC327, BC328

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

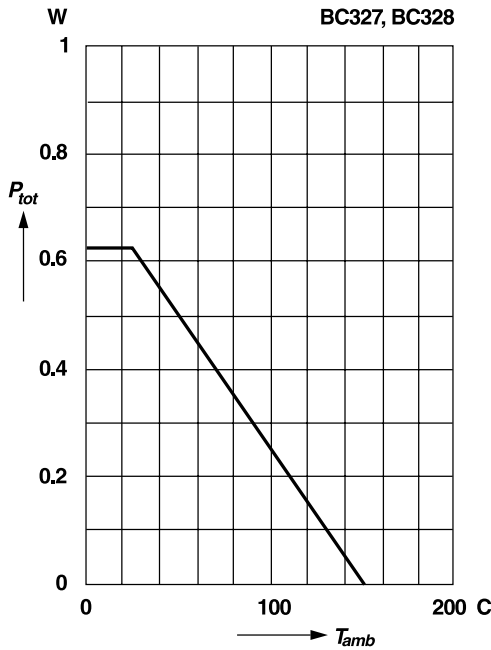
	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$ Current Gain Group-16 -25 -40	h_{FE} h_{FE} h_{FE}	100 160 250	160 250 400	250 400 630	— — —
at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$ Current Gain Group-16 -25 -40	h_{FE} h_{FE} h_{FE}	60 100 170	130 200 320	— — —	— — —
Thermal Resistance Junction to Ambient Air	R_{thJA}	—	—	200 ¹⁾	K/W
Collector-Emitter Cutoff Current at $-V_{CE} = 45\text{ V}$ at $-V_{CE} = 25\text{ V}$ at $-V_{CE} = 45\text{ V}$, $T_{amb} = 125\text{ °C}$ at $-V_{CE} = 25\text{ V}$, $T_{amb} = 125\text{ °C}$	BC327 BC328 BC327 BC328 $-I_{CES}$ $-I_{CES}$ $-I_{CES}$ $-I_{CES}$	— — — —	2 2 — —	100 100 10 10	nA nA μA μA
Collector-Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	BC327 BC328 — $V_{(BR)CEO}$ — $V_{(BR)CEO}$	45 25	— —	— —	V V
Collector-Emitter Breakdown Voltage at $-I_C = 0.1\text{ mA}$	BC327 BC328 — $V_{(BR)CES}$ — $V_{(BR)CES}$	50 30	— —	— —	V V
Emitter-Base Breakdown Voltage at $-I_E = 0.1\text{ mA}$	— $V_{(BR)EBO}$	5	—	—	V
Collector Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CEsat}$	—	—	0.7	V
Base-Emitter Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$	$-V_{BE}$	—	—	1.2	V
Gain-Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 50\text{ MHz}$	f_T	—	100	—	MHz
Collector-Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{CBO}	—	12	—	pF

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

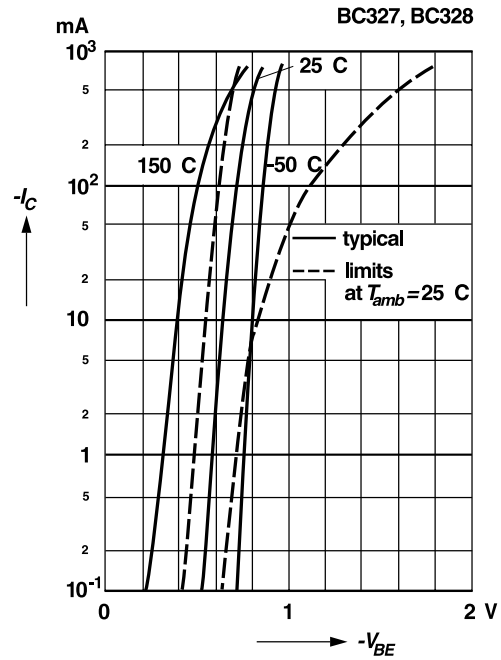
RATINGS AND CHARACTERISTIC CURVES BC327, BC328

Admissible power dissipation versus ambient temperature

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

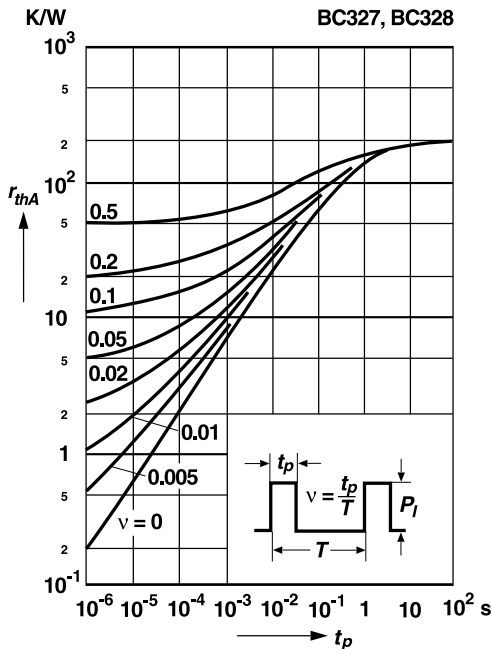


Collector current versus base-emitter voltage

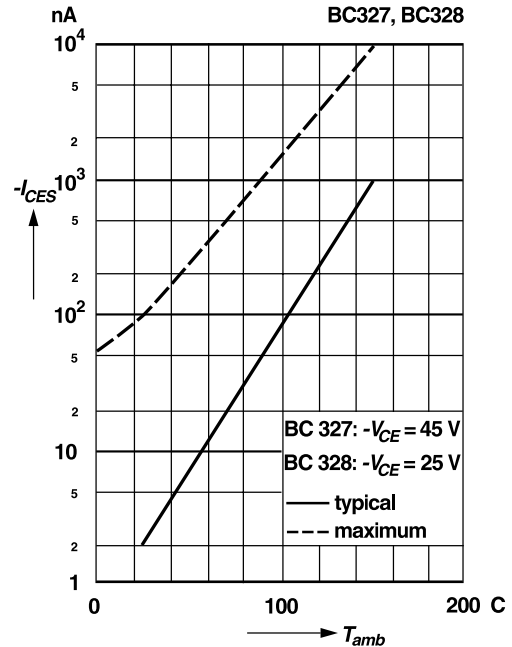


Pulse thermal resistance versus pulse duration

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

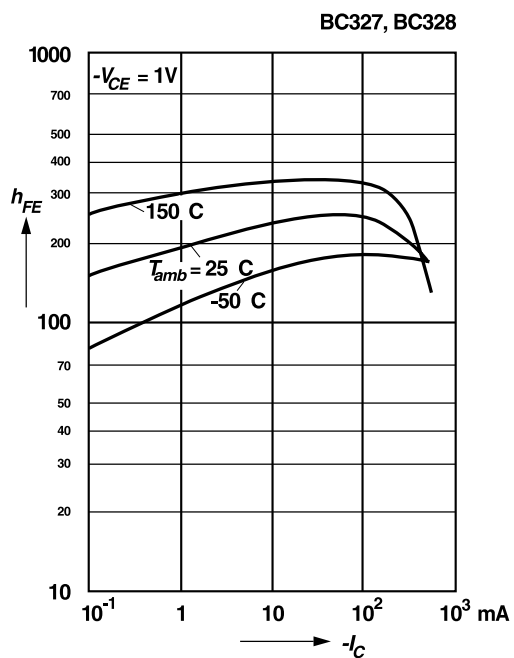


Collector-emitter cutoff current versus ambient temperature

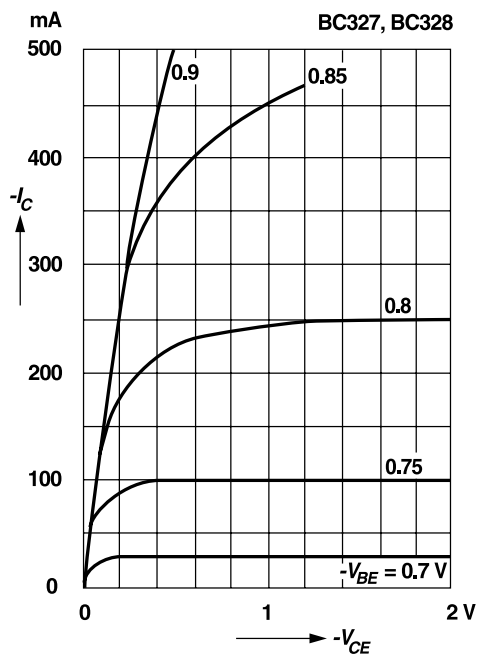


RATINGS AND CHARACTERISTIC CURVES BC327, BC328

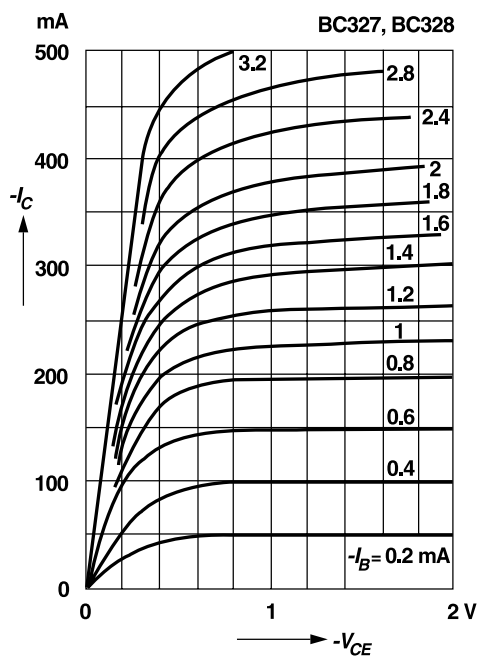
DC current gain
versus collector current



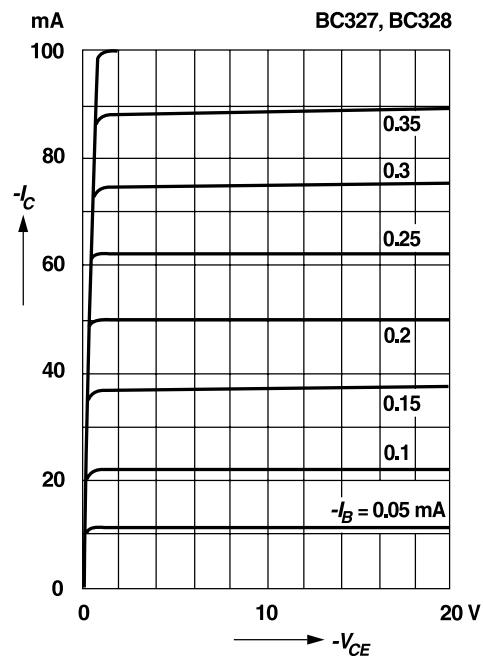
Common emitter
collector characteristics



Common emitter
collector characteristics

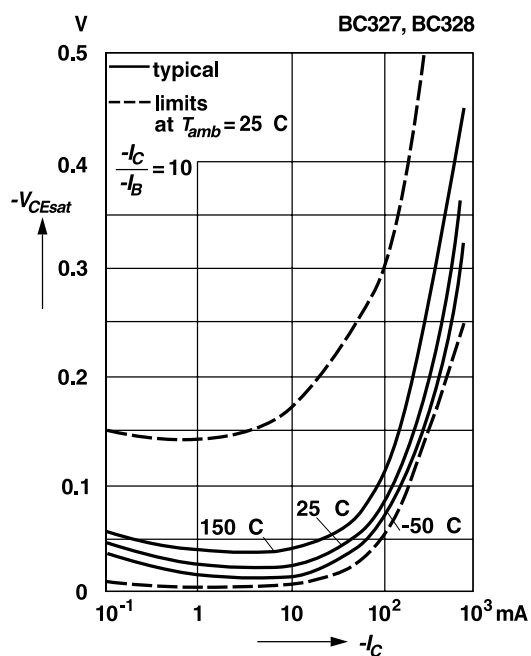


Common emitter
collector characteristics

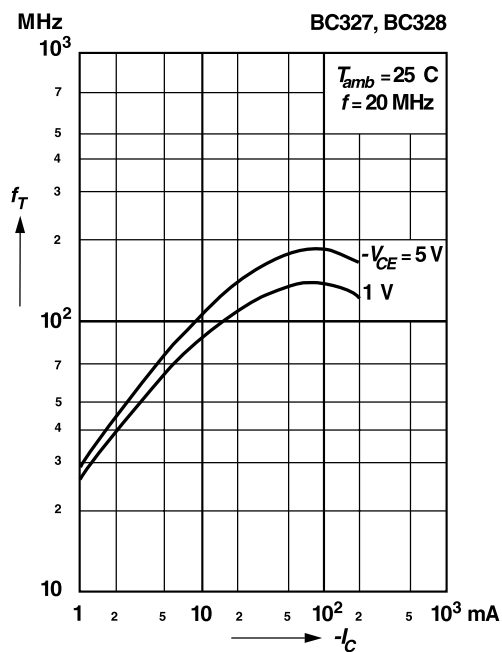


RATINGS AND CHARACTERISTIC CURVES BC327, BC328

Collector saturation voltage
versus collector current



Gain-bandwidth product
versus collector current



Base saturation voltage
versus collector current

